

Final Product/Process Change Notification Document #:FPCN25572X28

Issue Date:13 Feb 2024

Title of Change:	'	Update to FPCN25572X - Wafer Fab Site Addition of Vanguard International Semiconductor, Taiwan an Alternate Fab Site for FXMA2102L8X and FXMA108BQX.		
Proposed First Ship date:	20 May 2024 or earlier	if approved by customer		
Contact Information:	Contact your local onse	emi Sales Office or <u>logic.fpcn@onsemi.com</u>		
PCN Samples Contact:	Sample requests are to Initial PCN or Final PCN Samples delivery timin	Contact your local onsemi Sales Office. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.		
Additional Reliability Data:	Contact your local onse	Contact your local onsemi Sales Office or Changkit.Mok@onsemi.com		
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. onsemi will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact PCN.Support@onsemi.com			
Marking of Parts/ Traceability of Change:	Custom source on label will show TW instead of US to indicate new die source from Vanguard. Changed material may be identified by plant code or lot code too.			
Change Category:	Wafer Fab Change			
Change Sub-Category(s): Manufacturing Site Tra		ransfer, Datasheet/Product Doc change		
Sites Affected:	<u>.</u>			
onsemi Sites		External Foundry/Subcon Sites		
None		Vanguard International Semiconductor, Taiwan		

Description and Purpose:

With reference to FPCN25572X, this FPCN presents the information solely for FXMA2102L8X and FXMA108BQX part numbers.

This notification includes the pertinent reliability data.

	From	т	'o
Fab Site	Diodes Incorporated (Diodes)	Vanguard International Semiconductor (VIS)	Diodes Incorporated (Diodes)

There is no product marking change as a result of this change.

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Reliability Data Summary:

QV DEVICE NAME: FXMA2102L8X

RMS: S88603 / S91286

PACKAGE: UQFN8 1.6x1.6, 0.5P

Test	Specification	Condition	Interval	Results	
High Temperature Operating Life	JESD22-A108	Ta=125°C, 100 % max rated Vcc	1008 hrs	0/231	
High Temperature Storage Life	JESD22-A103	Ta= 150°C	1008 hrs	0/231	
Early Life Failure Rate	JESD22-A108	Ta=125°C, 100 % max rated Vcc	48 hrs	0/3120	
Preconditioning	J-STD-020 JESD-	MSL 1 @ 260°C, Pre TC, uHAST, HAST	_	0/693	
Freconditioning	A113	for surface mount pkgs only	_	0,093	
Temperature Cycling	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/231	
Highly Accelerated Stress Test	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/231	
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231	

QV DEVICE NAME: FXMA108BQX

RMS: S88604

PACKAGE: WQFN20 4.5x2.5, 0.5P

Test	Specification	Condition	Interval	Results
High Temperature Operating Life	JESD22-A108	Ta=125°C, 100 % max rated Vcc	1008 hrs	0/77
High Temperature Storage Life	JESD22-A103	Ta= 150°C	1008 hrs	0/77
Preconditioning	J-STD-020 JESD-	MSL 1 @ 260°C, Pre TC, uHAST, HAST		0/231
Freconditioning	A113	for surface mount pkgs only	-	0/231
Temperature Cycling	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
Highly Accelerated Stress Test	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/77
Unbiased Highly Accelerated Stress Test	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/77

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Electrical Characteristics Summary:

	From	То
Datasheet	Current Revision	New Revision

Datasheet Existing vs Updated for FXMA2102L8X:

Existing Datasheet

Features

- Bi-Directional Interface between Any Two Levels: 1.65 V to 5.5 V
- · Direction Control not Needed
- System GPIO Resources Not Required when OE Tied to V_{CCA}
- I²C 400 pF Buffer / Repeater
- I²C Bus Isolation
- A/B Port V_{OL} = 175 mV (Typical), V_{IL} = 150 mV, I_{OL} = 6 mA
- Open-Drain Inputs / Outputs
- Accommodates Standard–Mode and Fast–Mode I²C–Bus Devices
- Supports I²C Clock Stretching & Multi-Master
- · Fully Configurable: Inputs and Outputs Track VCC
- Control Input (OE) Referenced to V_{CCA}.
- Non-Preferential Power-Up; Either V_{CC} May Be Powered-Up First
- $\bullet\,$ Outputs Switch to 3–State if Either V_{CC} is at GND
- Tolerant Output Enable: 5 V
- Packaged in 8–Terminal Leadless MicroPak ™ (1.6 mm x 1.6 mm) and Ultrathin MLP (1.2 mm x 1.4 mm)
- ESD Protection Exceeds:
- 8 kV HBM ESD (per JESD22-A114)
- 2 kV CDM (per JESD22- C101)

Updated Datasheet

Features

- Bi-Directional Interface between Any Two Levels: 1.65 V to 5.5 V
- · Direction Control not Needed
- · System GPIO Resources Not Required when OE Tied to VCCA
- I²C 400 pF Buffer / Repeater
- I²C Bus Isolation
- A/B Port $V_{OL} = 175 \text{ mV}$ (Typical), $V_{IL} = 150 \text{ mV}$, $I_{OL} = 6 \text{ mA}$
- Open-Drain Inputs / Outputs
- Accommodates Standard-Mode and Fast-Mode I²C-Bus Devices
- Supports I²C Clock Stretching & Multi-Master
- $\bullet\,$ Fully Configurable: Inputs and Outputs Track V_{CC}
- Control Input (OE) Referenced to V_{CCA}.
- Non-Preferential Power-Up; Either V_{CC} May Be Powered-Up First
- $\bullet~$ Outputs Switch to 3-State if Either V_{CC} is at GND
- Tolerant Output Enable: 5 V
- Packaged in 8–Terminal Leadless MicroPak™ (1.6 mm x 1.6 mm) and Ultrathin MLP (1.2 mm x 1.4 mm)
- ESD Protection Exceeds:

• 5 kV HBM ESD (per JESD22–A114)

2 kV CDM (per JESD22- C101)

Existing Datasheet

Symbol	P	arameter	Min	Max	Uni
V _{CCA} , V _{CCB}	Supply Voltage		-0.5	7.0	V
VIN	DC Input Voltage	A Port	-0.5	7.0	
		B Port	-0.5	7.0	
		Control Input (OE)	-0.5	7.0	
V _O	Output Voltage (Note 2)	An Outputs 3-State	-0.5	7.0	٧
		B _n Outputs 3-State	-0.5	7.0	
		An Outputs Active	-0.5	V _{CCA} + 0.5 V	
		B _n Outputs Active	-0.5	V _{CCB} + 0.5 V	
I _{IK}	DC Input Diode Current	At V _{IN} < 0 V	-	-50	m/
loк	DC Output Diode Current	At V _O < 0 V	-	-50	m/
		At V _O > V _{CC}	-	+50	
I _{OH} / I _{OL}	DC Output Source/Sink Current	•	-50	+50	m/
lcc	DC V _{CC} or Ground Current per Sup	ply Pin	-	±100	m/
PD	Power Dissipation	At 400 KHz	-	0.129	m۷
T _{STG}	Storage Temperature Range	•	-65	+150	°C
ESD	Electrostatic Discharge Capability	Human Body Model, JESD22-A114	-	8	kV
		Charged Device Mode, JESD22-C101	-	2	

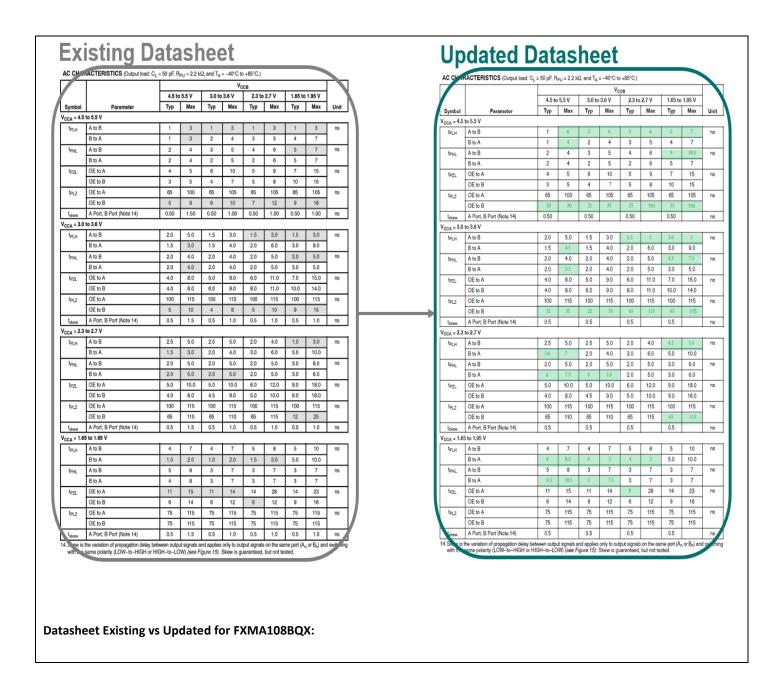
Updated Datasheet

Symbol	Parameter			Max	Unit
V _{CCA} , V _{CCB}	Supply Voltage		-0.5	7.0	V
VIN	DC Input Voltage	A Port	-0.5	7.0	
		B Port	-0.5	7.0	
		Control Input (OE)	-0.5	7.0	
V _O Output	Output Voltage (Note 2)	An Outputs 3-State	-0.5	7.0	V
		B _n Outputs 3-State	-0.5	7.0	
		An Outputs Active	-0.5	V _{CCA} + 0.5 V	
		B _n Outputs Active	-0.5	V _{CCB} + 0.5 V	
l _{IK}	DC Input Diode Current	At V _{IN} < 0 V	-	-50	mA
I _{OK}	DC Output Diode Current	At Vo < 0 V	-	-50	mA
		At V _O > V _{CC}	-	+50	
I _{OH} / I _{OL}	DC Output Source/Sink Current		-50	+50	mA
lcc	DC V _{CC} or Ground Current per Sup	ply Pin	-	±100	mA
PD	Power Dissipation	At 400 KHz	-	0.129	mW
T _{STG}	Storage Temperature Range		-65	+150	°C
ESD	Electrostatic Discharge Capability	Human Body Model, JESD22-A114	-	5	kV
		Charged Device Mode, JESD22-C101	-	2	

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Existing Datasheet

Features

- Bi-Directional Interface between Two Levels from 1.65 V to 5.5 V
- Fully Configurable: Inputs and Outputs Track V_{CC}
- Non-Preferential Power-Up; Either V_{CC} May Be Powered-Up First
- Outputs Remain in 3-State Until Active V_{CC} Level is Reached
- Outputs Switch to 3-State if Either V_{CC} is at GND
- Power-Off Protection
- Bus Hold On Data Inputs Eliminates the Need for Pull-Up Resistors
- Control Input (/OE) is Referenced to V_{CCA} Voltage
- Packaged in 20–Terminal WQFN
- Direction Control Not Needed
- 80 Mbps Throughput when Translating between 2.5 V and 5.0 V
- ESD Protection Exceeds:
 - 8 kV Human Body Model (B Port I/O to GND) (JESD22-A114 & Mil Std 883e 3015.7)
 - 5 kV Human Body Model (A Port I/O to GND) (JESD22-A114 & Mil Std 883e 3015.7)
 - 2 kV Charged Device Model (ESD STM 5.3) (JESD22-C101)

Updated Datasheet

Features

- Bi-Directional Interface between Two Levels from 1.65 V to 5.5 V
- $\bullet\,$ Fully Configurable: Inputs and Outputs Track V_{CC}
- Non-Preferential Power-Up; Either V_{CC} May Be Powered-Up First
- Outputs Remain in 3-State Until Active V_{CC} Level is Reached
- \bullet Outputs Switch to 3-State if Either V_{CC} is at GND
- Power-Off Protection
- Bus Hold On Data Inputs Eliminates the Need for Pull-Up Resistors
- ullet Control Input (/OE) is Referenced to V_{CCA} Voltage
- Packaged in 20-Terminal WQFN
- Direction Control Not Needed
- 80 Mbps Throughput when Translating between 2.5 V and 5.0 V
- · ESD Protection Exceeds:
 - 8 kV Human Body Model (B Port I/O to GND) (JESD22-A114 & Mil Std 883e 3015.7)
 - 4 kV Human Body Model (A Port I/O to GND)
 (JESD22-A114 & Mil Std 883e 3015.7)
 - 2 kV Charged Device Model (ESD STM 5.3) (JESD22-C101)

Existing Datasheet

Symbol		Parameter	Condition	Min	Max	Un
V _{CC}	Supply Voltage		V _{CCA}	-0.5	7.0	٧
			V _{CCB}	-0.5	7.0	
V _{IN}	DC Input Voltage		I/O Side A and B	-0.5	7.0	٧
		Control Input (/OE)	-0.5	7.0		
V _O Output Voltage			Output 3-State	-0.5	7.0	٧
		Output Active (An) (Note 1)	-0.5	V _{CCA} + 0.5		
			Output Active (Bn) (Note 1)	-0.5	V _{CCB} + 0.5	
I _{IK}	DC Input Diode Current		V _{IN} < 0 V		-50	m
I _{OK} DC Output Diode Currer		Current	V _O < 0 V		-50	m
			V _O > V _{CC}		+50	
I _{OH} /I _{OL}	DC Output Source/Sink Current			-50	+50	m
Icc	DC V _{CC} or Ground	Current (Per Supply Pin)			±100	m
T _{STG}	Storage Temperature Range			-65	+150	۰(
ESD	Discharge	Human Body Model, JESD22- A114, and Mil Std 883e 3015.7	B Port I/O to GND		8000	٧
	Capability	Human Body Model, JESD22- A114 and Mil Std 883e 3015.7	A Port I/O to GND		5000	
	Charged Device Model, JESD22-		C101 per ESD STM 5.3		2000	

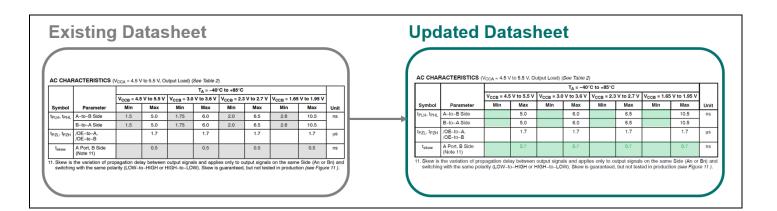
Updated Datasheet

Symbol		Parameter	Condition	Min	Max	Unit
V _{CC}	Supply Voltage		V _{CCA}	-0.5	7.0	V
			V _{CCB}	-0.5	7.0	
VIN	V _{IN} DC Input Voltage		I/O Side A and B	-0.5	7.0	٧
			Control Input (/OE)	-0.5	7.0	
Vo	Output Voltage		Output 3-State	-0.5	7.0	V
			Output Active (An) (Note 1)	-0.5	V _{CCA} + 0.5	
		Output Active (Bn) (Note 1)	-0.5	V _{CCB} + 0.5		
l _{IK}	DC Input Diode Current		V _{IN} < 0 V		-50	mA
lok	I _{OK} DC Output Diode Current		V _O < 0 V		-50	mA
			V _O > V _{CC}		+50	
I _{OH} /I _{OL}	DC Output Source	DC Output Source/Sink Current			+50	m/
loc	DC V _{CC} or Ground	Current (Per Supply Pin)			±100	mA
TSTG	Storage Temperatu	re Range		-65	+150	°C
ESD	Discharge	Human Body Model, JESD22- A114, and Mil Std 883e 3015.7	B Port I/O to GND		8000	٧
	Capability	Human Body Model, JESD22- A114 and Mil Std 883e 3015.7	A Port I/O to GND		4000	
	I	Charged Device Model, JESD22-	C101 per ESD STM 5.3		2000	

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List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
FXMA108BQX	FXMA108BQX
FXMA2102L8X	FXMA2102L8X

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